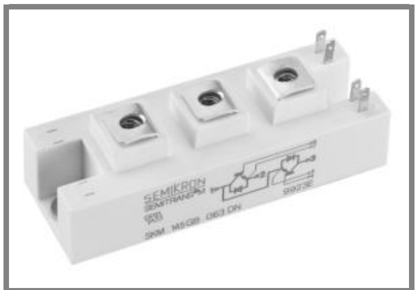
# SKM 100GB125DN




**SEMITRANS® 2N**

## Ultra Fast IGBT Module

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### Features

- N channel, homogeneous Si
- Low inductance case
- Short tail current with low temperature dependence
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### Typical Applications*

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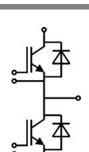
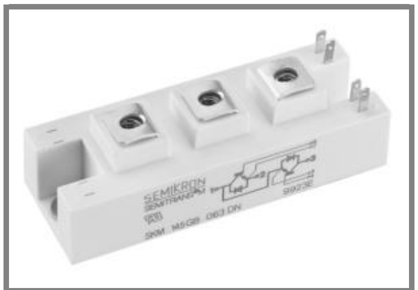
- Electronic welders at $f_{sw}$ > 20 kHz



**GB**

| **Absolute Maximum Ratings** | | $T_c$ = 25 °C, unless otherwise specified | | |
|---|---|---|---|---|
| **Symbol** | **Conditions** | | **Values** | **Units** |
| **IGBT** | | | | |
| $V_{CES}$ | $T_j$ = 25 °C | | 1200 | V |
| $I_C$ | $T_j$ = 150 °C | $T_{case}$ = 25 °C | 100 | A |
| | | $T_{case}$ = 85 °C | 80 | A |
| $I_{CRM}$ | $I_{CRM}$=2x$I_{Cnom}$ | | 150 | A |
| $V_{GES}$ | | | ± 20 | V |
| $t_{psc}$ | $V_{CC}$ = 600 V; $V_{GE} \leq$ 20 V; $V_{CES}$ < 1200 V | $T_j$ = 125 °C | 10 | µs |
| **Inverse Diode** | | | | |
| $I_F$ | $T_j$ = 150 °C | $T_{case}$ = 25 °C | 95 | A |
| | | $T_{case}$ = 80 °C | 65 | A |
| $I_{FRM}$ | $I_{FRM}$=2x$I_{Fnom}$ | | 150 | A |
| $I_{FSM}$ | $t_p$ = 10 ms; sin. | $T_j$ = 150 °C | 720 | A |
| **Module** | | | | |
| $I_{t(RMS)}$ | | | 200 | A |
| $T_{vj}$ | | | - 40 ... + 150 | °C |
| $T_{stg}$ | | | 125 | °C |
| $V_{isol}$ | AC, 1 min. | | 4000 | V |

| **Characteristics** | | | $T_c$ = 25 °C, unless otherwise specified | | | |
|---|---|---|---|---|---|---|
| **Symbol** | **Conditions** | | **min.** | **typ.** | **max.** | **Units** |
| **IGBT** | | | | | | |
| $V_{GE(th)}$ | $V_{GE} = V_{CE}$, $I_C$ = 2 mA | | 4,5 | 5,5 | 6,5 | V |
| $I_{CES}$ | $V_{GE}$ = 0 V, $V_{CE} = V_{CES}$ | $T_j$ = 25 °C | | 0,15 | 0,45 | mA |
| | | $T_j$ = 125 °C | | | | mA |
| $V_{CE0}$ | | $T_j$ = 25 °C | | | | V |
| | | $T_j$ = 125 °C | | | | V |
| $r_{CE}$ | $V_{GE}$ = 15 V | $T_j$ = 25°C | | | | mΩ |
| | | $T_j$ = 125°C | | | | mΩ |
| $V_{CE(sat)}$ | $I_{Cnom}$ = 75 A, $V_{GE}$ = 15 V | $T_j$ = °$C_{chiplev.}$ | | 3,3 | 3,85 | V |
| $C_{ies}$ | $V_{CE}$ = 25, $V_{GE}$ = 0 V | f = 1 MHz | | 5 | 6,6 | nF |
| $C_{oes}$ | | | | 0,72 | 0,9 | nF |
| $C_{res}$ | | | | 0,38 | 0,5 | nF |
| $Q_G$ | $V_{GE}$ = 0 - +20V | | | 650 | | nC |
| $R_{Gint}$ | $T_j$ = °C | | | 5 | | Ω |
| $t_{d(on)}$ | $R_{Gon}$ = 8 Ω | $V_{CC}$ = 600V | | 80 | | ns |
| $t_r$ | | $I_C$= 75A | | 40 | | ns |
| $E_{on}$ | | $T_j$ = 125 °C | | 9 | | mJ |
| $t_{d(off)}$ | $R_{Goff}$ = 8 Ω | $V_{GE}$ = ± 15V | | 360 | | ns |
| $t_f$ | | | | 20 | | ns |
| $E_{off}$ | | | | 3,5 | | mJ |
| $R_{th(j-c)}$ | per IGBT | | | | 0,18 | K/W |



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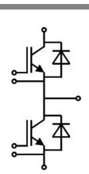

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| Characteristics | | | | | | |
|---|---|---|---|---|---|---|
| **Symbol** | **Conditions** | | **min.** | **typ.** | **max.** | **Units** |
| **Inverse Diode** | | | | | | |
| $V_F = V_{EC}$ | $I_{Fnom}$ = 75 A; $V_{GE}$ = 0 V | $T_j$ = 25 °C$_{chiplev.}$ | | 2 | 2,5 | V |
| | | $T_j$ = 125 °C$_{chiplev.}$ | | 1,8 | | V |
| $V_{F0}$ | | $T_j$ = °C | | 1,1 | 1,2 | V |
| $r_F$ | | $T_j$ = °C | | 12 | 17,3 | mΩ |
| $I_{RRM}$ | $I_F$ = 75 A | $T_j$ = 125 °C | | 50 | | A |
| $Q_{rr}$ | di/dt = 800 A/µs | | | 11,5 | | µC |
| $E_{rr}$ | $V_{GE}$ = 0 V; $V_{CC}$ = 600 V | | | | | mJ |
| $R_{th(j-c)D}$ | per diode | | | | 0,5 | K/W |
| **Module** | | | | | | |
| $L_{CE}$ | | | | 20 | 25 | nH |
| $R_{CC'+EE'}$ | res., terminal-chip | $T_{case}$= 25 °C | | 0,75 | | mΩ |
| | | $T_{case}$= 125 °C | | 1 | | mΩ |
| $R_{th(c-s)}$ | per module | | | | 0,05 | K/W |
| $M_s$ | to heat sink M6 | | 3 | | 5 | Nm |
| $M_t$ | to terminals M5 | | 2,5 | | 5 | Nm |
| w | | | | | 160 | g |

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.

 

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| $Z_{th}$ Symbol | Conditions | Values | Units |
|---|---|---|---|
| $Z_{th(j-c)I}$ | | | |
| $R_i$ | i = 1 | 95 | mk/W |
| $R_i$ | i = 2 | 65 | mk/W |
| $R_i$ | i = 3 | 17,5 | mk/W |
| $R_i$ | i = 4 | 2,5 | mk/W |
| $tau_i$ | i = 1 | 0,0327 | s |
| $tau_i$ | i = 2 | 0,008 | s |
| $tau_i$ | i = 3 | 0,0017 | s |
| $tau_i$ | i = 4 | 0,008 | s |
| $Z_{th(j-c)D}$ | | | |
| $R_i$ | i = 1 | 300 | mk/W |
| $R_i$ | i = 2 | 160 | mk/W |
| $R_i$ | i = 3 | 36 | mk/W |
| $R_i$ | i = 4 | 4 | mk/W |
| $tau_i$ | i = 1 | 0,054 | s |
| $tau_i$ | i = 2 | 0,001 | s |
| $tau_i$ | i = 3 | 0,0015 | s |
| $tau_i$ | i = 4 | 0,1 | s |

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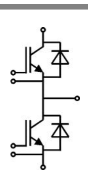

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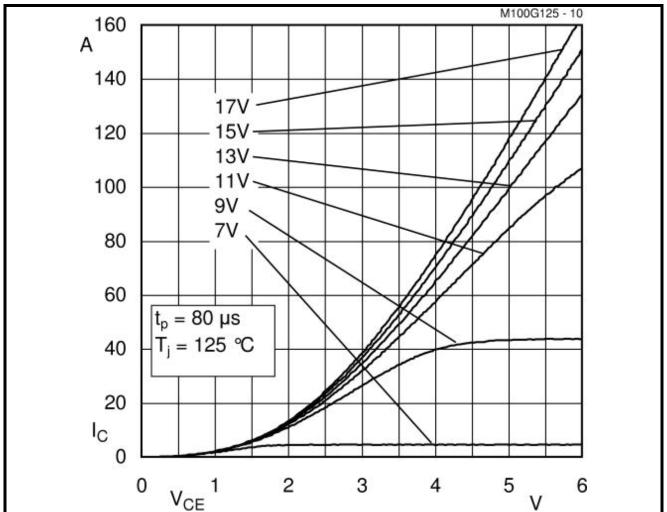


Fig. 1 Typ. output characteristic, inclusive $R_{CC'+ EE'}$

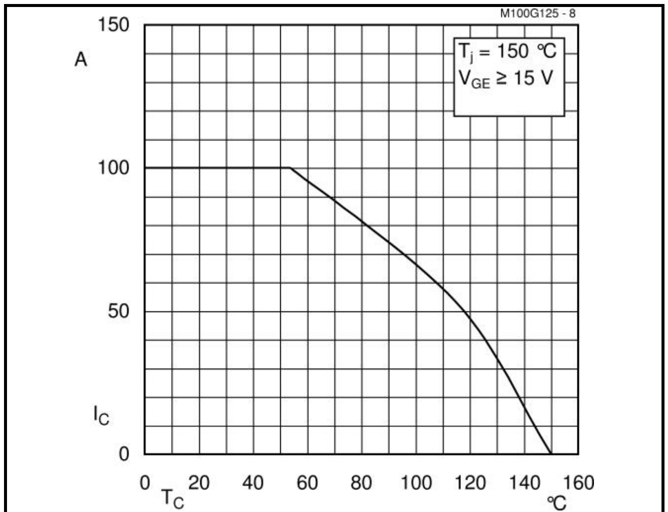


Fig. 2 Rated current vs. temperature $I_C$ = f ($T_C$)

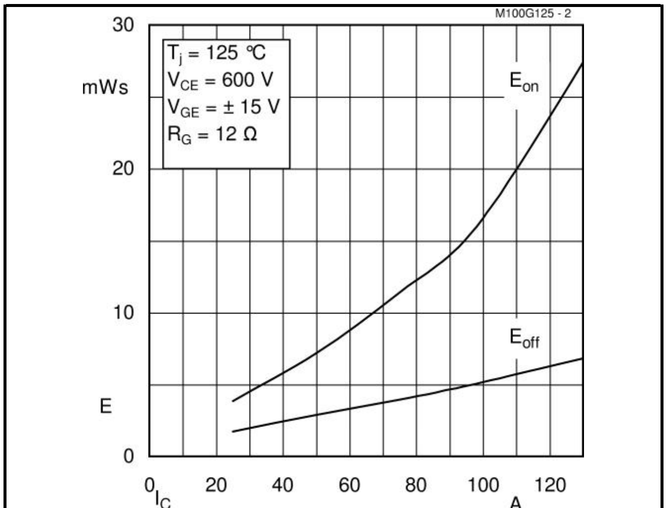


Fig. 3 Typ. turn-on /-off energy = f ($I_C$)

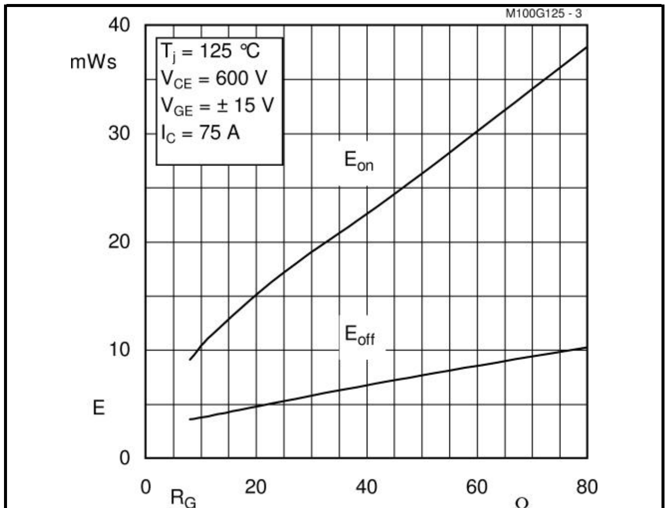


Fig. 4 Typ. turn-on /-off energy = f ($R_G$)

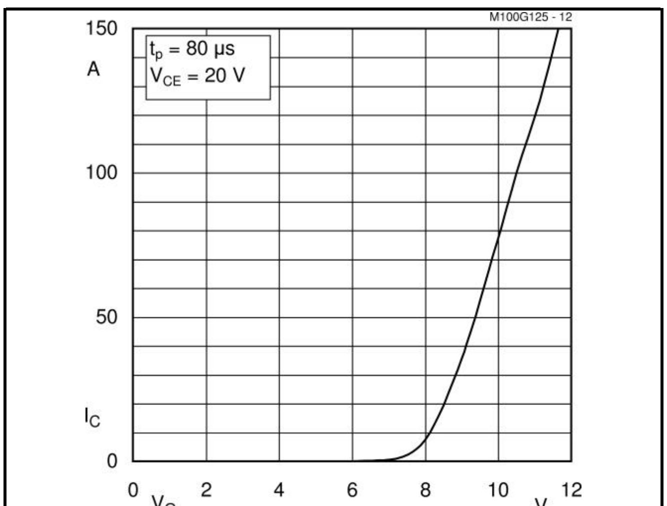


Fig. 5 Typ. transfer characteristic

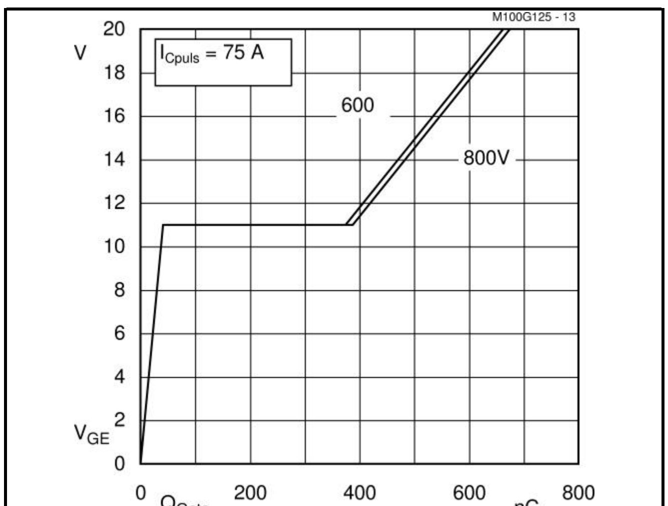


Fig. 6 Typ. gate charge characteristic

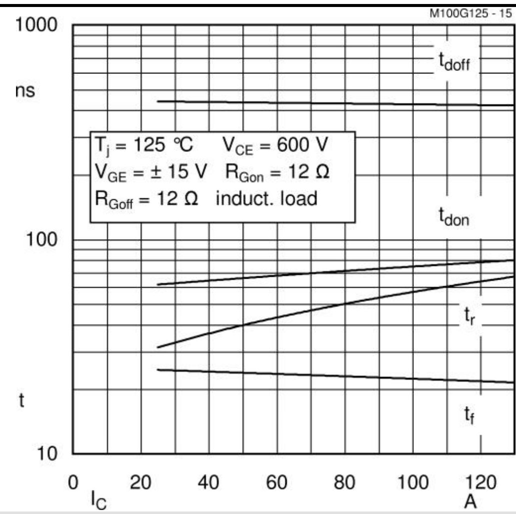



Fig. 7 Typ. switching times vs. $I_C$

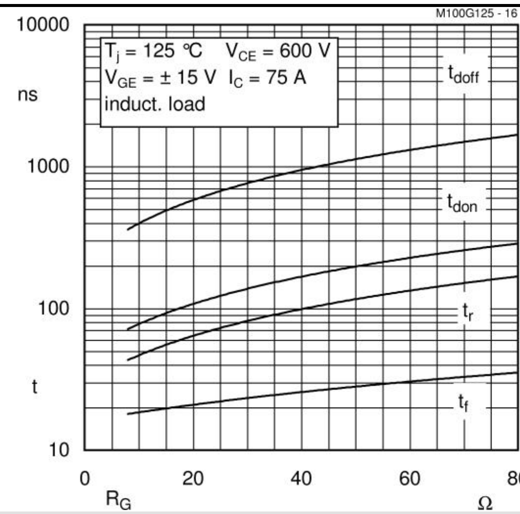



Fig. 8 Typ. switching times vs. gate resistor $R_G$

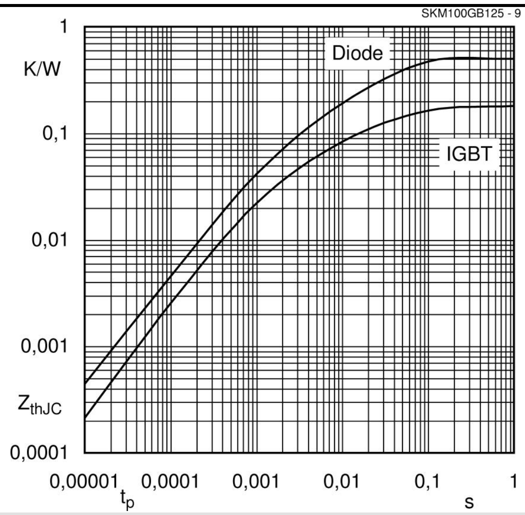



Fig. 9 Transient thermal impedance

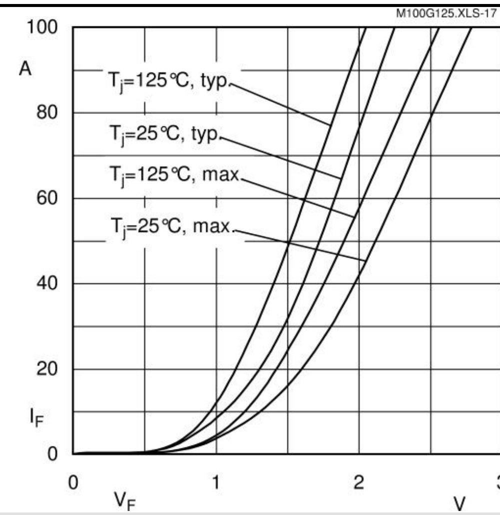



Fig. 10 CAL diode forward characteristic

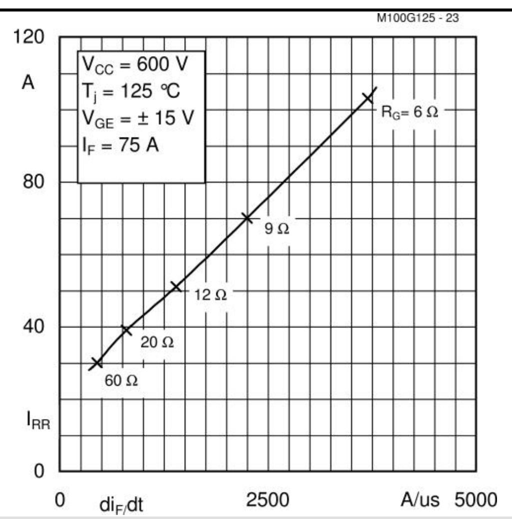



Fig. 11 Typ. CAL diode peak reverse recovery current

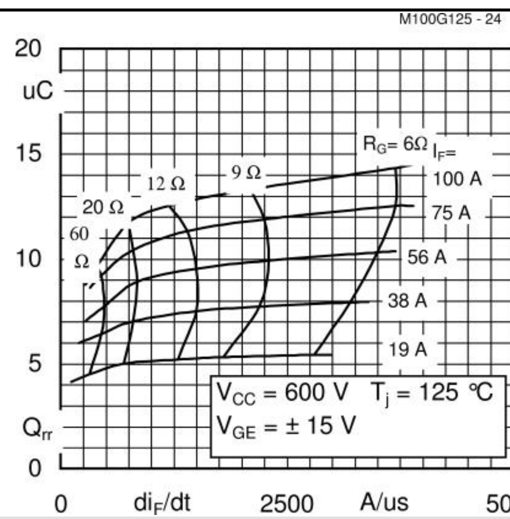
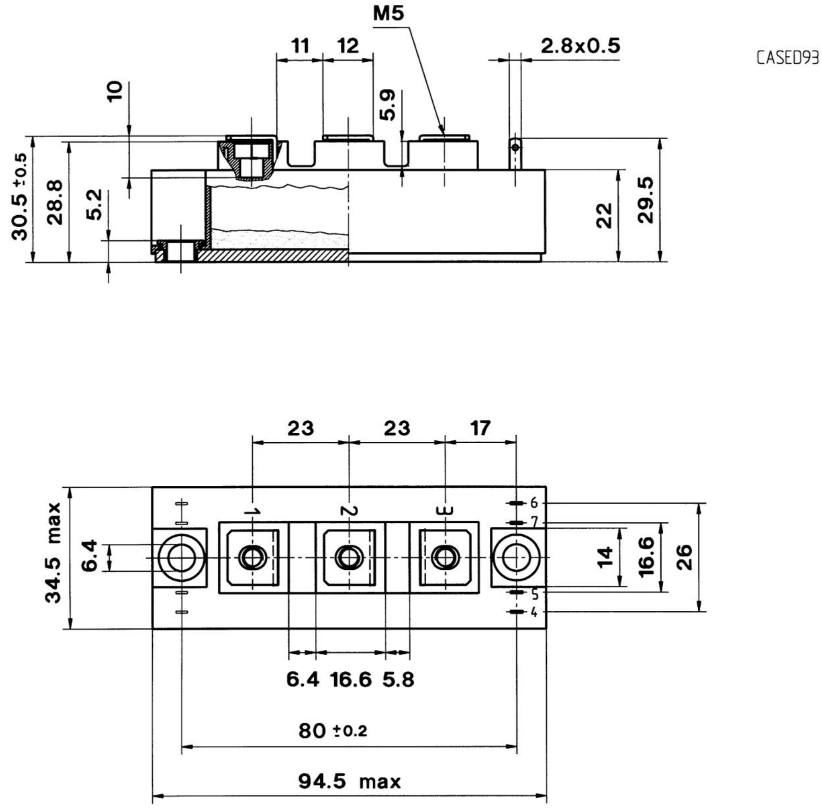


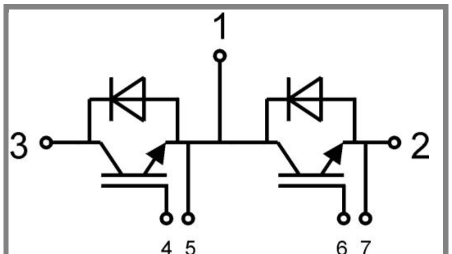

Fig. 12 Typ. CAL diode peak reverse recovery charge

UL Recognized File 63 532




Case D 93




GB Case D 93